Digital transistors (built-in resistors) DTB114EK / DTB114ES

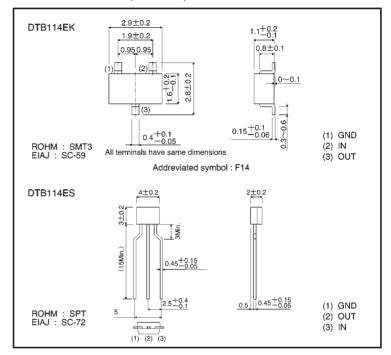
Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.

Structure

PNP digital transistor (Built-in resistor type)

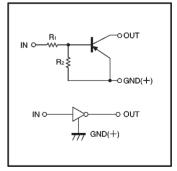
External dimensions (Units: mm)



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits(D	Unit	
	Symbol	К	S	Offic
Supply voltage	Vcc	— 50		V
Input voltage	Vin	−40~+10		٧
Output current	lc	—500		mA
Power dissipation	Pd	200	300	mW
Junction temperature	Tj	150		°C
Storage temperature	Tstg	−55∼ +150		°C

Equivalent circuit



(96-290-B114E)

• Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input voltage	VI(off)	_	_	-0.5	٧	Vcc=-5V, lo=100 μA	
	VI(on)	-3	_	_		Vo=-0.3V, Io=-10mA	
Output voltage	V _{O(on)}	_	-0.1	-0.3	٧	Io/li=-50mA/-2.5mA	
Input current	lı	_	_	-0.88	mA	V _I =-5V	
Output current	IO(off)	_	_	-0.5	μΑ	Vcc=-50V, Vi=0V	
DC current gain	Gı	56	_	_	_	Vo=-5V, Io=-50mA	
Input resistance	R ₁	7	10	13	kΩ	_	
Resistance ratio	R2/R1	0.8	1	1.2	_	_	
Transition frequency	f⊤	_	200	_	MHz	Vc=−10V, l==5mA, f=100MHz *	

^{*} Transition frequency of the device

Packaging specifications

	Package	SMT3	SPT
	Packaging type	Taping	Taping
	Code	T146	TP
Part No.	Basic ordering unit (pieces)	3000	5000
DTB114EK		0	
DTB114ES			0

Electrical characteristic curves

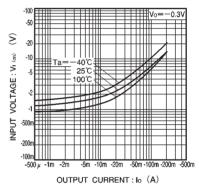


Fig.1 Input voltage vs. output current (ON characteristics)

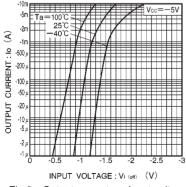


Fig.2 Output current vs. input voltage (OFF characteristics)

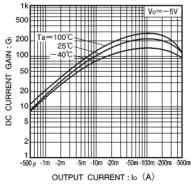


Fig.3 DC current gain vs. output current

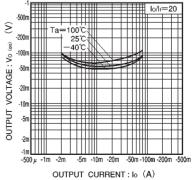


Fig.4 Output voltage vs. output current